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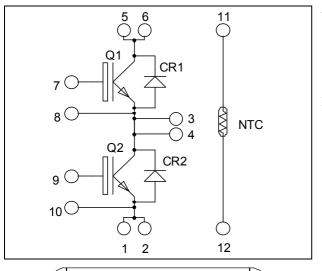
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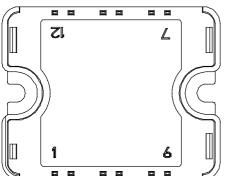




Phase leg NPT IGBT Power Module

$V_{CES} = 600V$ $I_{C} = 30A$ (a) $Tc = 80^{\circ}C$





Pins 1/2; 3/4; 5/6 must be shorted together

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit	
V _{CES}	Collector - Emitter Breakdown Voltage		600	V
т	Continuous Collector Current	$T_C = 25^{\circ}C$	42	
I _C	Continuous Conector Current	$T_C = 80^{\circ}C$	30	Α
I _{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	100	
V _{GE}	Gate – Emitter Voltage		±20	V
PD	Maximum Power Dissipation	$T_C = 25^{\circ}C$	140	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	60A@500V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Non Punch Through (NPT) Fast IGBT
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 100 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
 - Very low stray inductance
 - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant



All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics Symbol **Characteristic Test Conditions** Min Тур Max Unit $V_{GE} = 0\overline{V}$ $T_i = 25^{\circ}C$ 250 ICES Zero Gate Voltage Collector Current μΑ $V_{CE} = 600V$ $T_i = 125^{\circ}C$ 500 $T_i = 25^{\circ}C$ $V_{GE} = 15V$ 1.7 2.45 2.0 V_{CE(on)} V Collector Emitter on Voltage $I_{C} = 30A$ $T_i = 125^{\circ}C$ 2.2 $V_{GE} = V_{CE}, I_C = 1 \text{mA}$ Gate Threshold Voltage V V_{GE(th)} 4 6 I_{GES} Gate - Emitter Leakage Current $V_{GE} = 20V, V_{CE} = 0V$ 400 nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$			1350		
Coes	Output Capacitance				193		pF
C _{res}	Reverse Transfer Capacitance	f = 1 MHz			120		
Qg	Total gate Charge	$V_{GE} = 15V$			99		nC
Q _{ge}	Gate – Emitter Charge	$V_{Bus} = 300V$			10		
Q _{gc}	Gate – Collector Charge	$I_C = 30A$		60			
T _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = 15V$			30		
Tr	Rise Time				12		ns
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 400V$ $I_C = 30A$		80			
$T_{\rm f}$	Fall Time	$R_G = 6.8\Omega$		15			
T _{d(on)}	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = 15V$ $V_{Bus} = 400V$ $I_C = 30A$ $R_G = 6.8\Omega$			32		ns
Tr	Rise Time				12		
T _{d(off)}	Turn-off Delay Time				90		
$T_{\rm f}$	Fall Time				21		
Eon	Turn-on Switching Energy	$V_{GE} = 15V$ $V_{Bus} = 400V$	$T_j = 125^{\circ}C$		0.3		mI
E _{off}	Turn-off Switching Energy	$I_{\rm C} = 30 \text{A}$ $R_{\rm G} = 6.8 \Omega$	$T_j = 125^{\circ}C$		0.8		mJ

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit	
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I _{RM}	Maximum Reverse Leakage Current	V _R =600V	$T_j = 25^{\circ}C$			25	μA
IRM			$T_{j} = 125^{\circ}C$			500	μΑ
$I_{\rm F}$	DC Forward Current		$Tc = 80^{\circ}C$		25		А
	Diode Forward Voltage	$I_F = 25A$			1.8	2.2	
V _F		$I_F = 50A$			2.2		V
		$I_F = 25A$	$T_j = 125^{\circ}C$		1.6		
t _{rr}	Reverse Recovery Time	$I_{F} = 25A$ $V_{R} = 400V$ $di/dt = 200A/\mu s$	$T_j = 25^{\circ}C$		30		ns
۹r			$T_j = 125^{\circ}C$		175		115
Q _{rr}	Reverse Recovery Charge		$T_j = 25^{\circ}C$		55		nC
Чт			$T_{j} = 125^{\circ}C$		485		ne

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Thermal and package characteristics

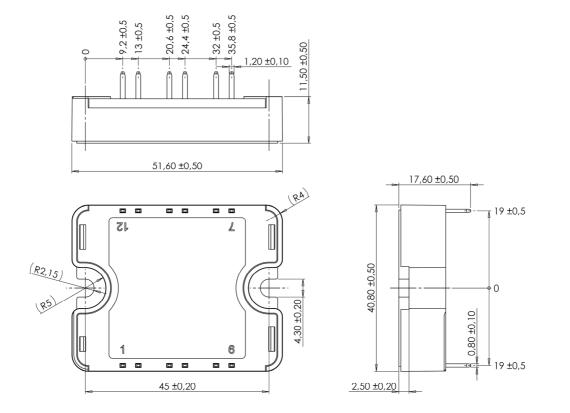
Symbol	Characteristic			Ν	Min	Тур	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance	IGB	Т			0.9	°C/W	
			Dio	de			1.4	C/ W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4	000			V
T _J	Operating junction temperature range			-	-40		150	
T _{STG}	Storage Temperature Range			-	-40		125	°C
T _C	Operating Case Temperature						100	
Torque	Mounting torque	To heatsin	nk N	М4	2		3	N.m
Wt	Package Weight						80	g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature
R_T: Thermistor value at T

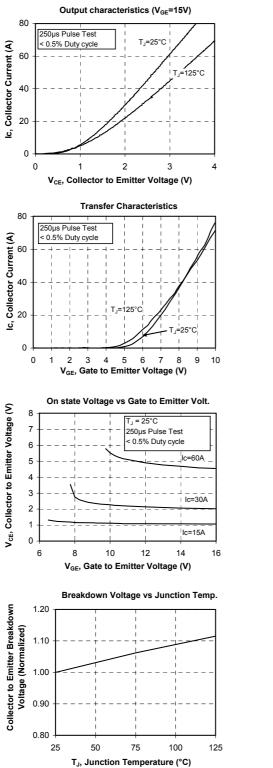
SP1 Package outline (dimensions in mm)



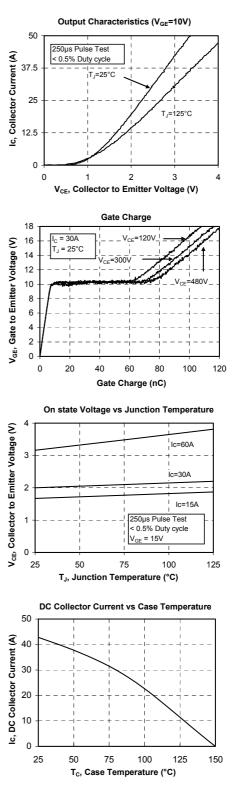
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com



Typical Performance Curve



APTGF30A60T1G



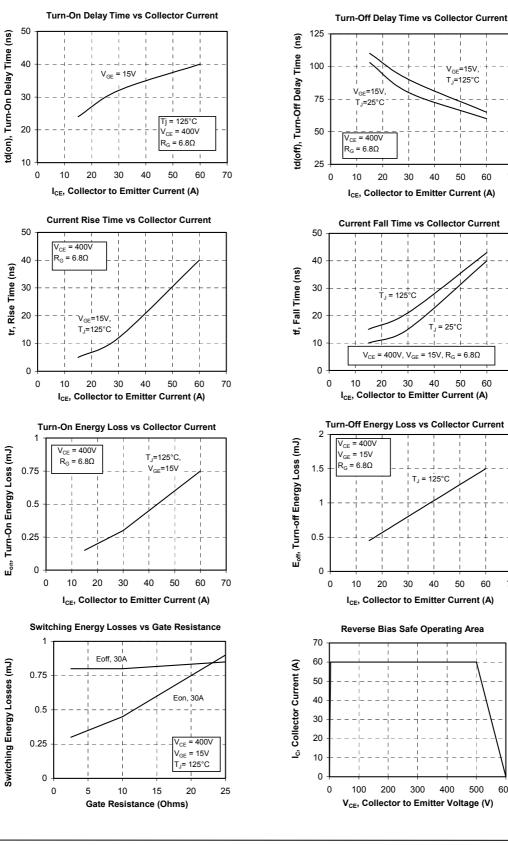


70

70

70

600





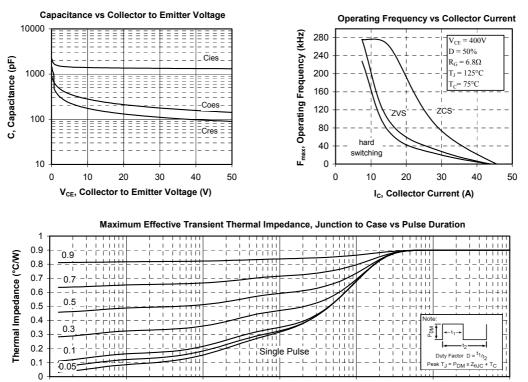
0.00001

0.0001

APTGF30A60T1G

1

10



0.001 0.01 0.1 Rectangular Pulse Duration (Seconds)

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